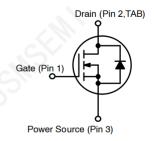


## **Features**

- ♦ High density cell design for low RDS(ON))
- ◆ Voltage controlled small signal switch
- ◆ Rugged and reliable
- ◆ ESD protected
- ◆ Device Marking Code





# MAXIMUM RATINGS (Ta = 25 °C)

SOT-323

Symbol	Parameter	Value	Units
V <sub>DS</sub>	Drain-source Voltage	60	V
Vgs	Gate-source Voltage	±20	V
<b>I</b> D	Continuous Drain Current	340	mA
Pd	Total Power Dissipation	200	mW
TJ	Junction Temperature	150	°C
T <sub>STG,</sub>	Storage Temperature	-55 to 150	°C
$R_{\theta}$ JA	Thermal Resistance from Junction to Ambient	625	°C/W

# ELECTRICAL CHARACTERISTICS (Ta = 25 °C) Static Characteristics

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
$V_{(BR)Dss}$	Drain-source Breakdown Voltage	V <sub>GS</sub> =0V,I <sub>D</sub> =250uA	60			V
$V_{GS(th)}$	Gate-Threshold Voltage (note 1)	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =1mA	1.0	.c.	2.5	٧
$\mathbf{I}_{GSS}$	Gate -body Leakage Current	$V_{DS}=0V,V_{GS}=\pm20V$			±10	uA
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> =48V,V <sub>GS</sub> =0V		37	1	uA
Rdson	Drain-source On-resistance (note 1)	V <sub>GS</sub> =4.5V,I <sub>D</sub> =200mA V <sub>GS</sub> =10V,I <sub>D</sub> =500mA			5.3 5.0	Ω
V <sub>SD</sub>	Diode Forward Voltage	V <sub>GS</sub> =0V,I <sub>S</sub> =300mA			1.5	V

## Dynamic Characteristics

Ciss	Input Capacitance	V <sub>DS</sub> =10V		40	
Coss	Output Capacitance	V <sub>GS</sub> =0V		30	pF
Crss	Reverse Transfer	f=1MHz	11/2	10	
<b>D</b> ),	Capacitance		(5)		



## **Switching Characteristics**

td(on)	Turn-on delay time	$V_{DD}$ =50V, $V_{GS}$ =10V, $R_L$ =250 $\Omega$ ,		10	ns
td(off)	Turn-off delay time	$R_{GS}=50 \Omega$ , $R_{GEN}=50 \Omega$		15	
trr	Reverse Recovery Time	Vgs=0V,Is=300mA,VR=25V, dls/dt=-100A/us	30	<b>U</b> /2	ns
Qr	Recovered Charge	Vgs=0V,Is=300mA,VR=25V	30		nC
		dls/dt=-100A/us			

## GATE-SOURCE ZENER DIODE

BVgso	Gate-Source	IGS=±1mA(Open Drain)	±21.5	±30	٧
	Breakdown Voltage				

#### DRAIN-SOURCE DIODE

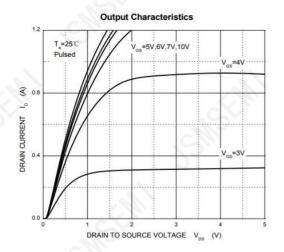
D10 (111 00	01.02 0.002					
VsD	Diode Forward Voltage(note 1)	Is=300mA, V <sub>GS</sub> = 0V			1.5	٧
<b>I</b> s	Continuous Diode				0.2	Α
	Forward Current					
Ism	Pulsed Diode	11/2		SY	0.53	Α
	Forward Current	3/4.	.6			

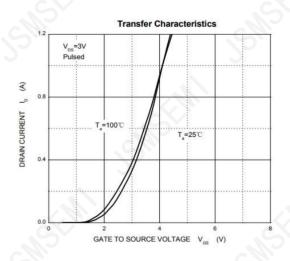
#### Note:

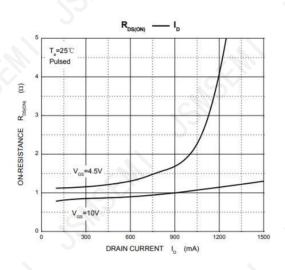
1. Pulse Test : Pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%.

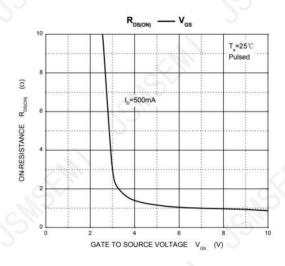


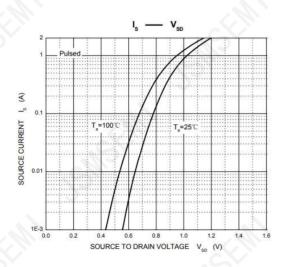
#### TYPICAL CHARACTERISTICS

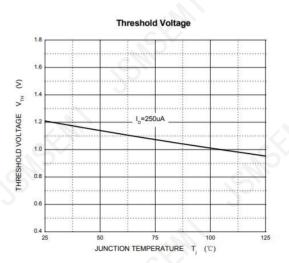








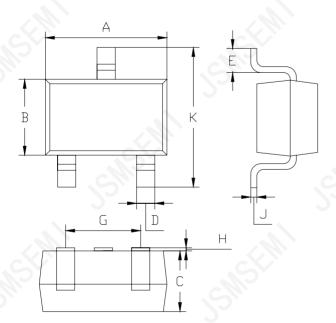






# **Package Information**

SOT-323



SOT-323					
Dim	Min	Max			
Α	1.8	2.2			
В	1.15	1.35			
С	1.0Typical				
D	0.15	0.35			
E	0.25	0.40			
G	1.2	1.4			
Н	0.02	0.1			
J	0.1Typical				
К	2.1 2.3				
All Dimensions in mm					



## **Revision History**

Rev.	Change	Date
V1.0	Initial version	2/23/2024
-11		

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